



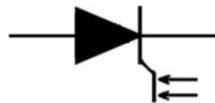
高端电力电子器件和装置制造商

TLI183-2000

脉冲光控晶闸管

- ◆ $V_{DRM} = \text{6000-6500 V}$
- ◆ $V_{RRM} = \text{6000-6500 V}$
- ◆ $I_{TRM} = \text{65 kA}$ ($t_p = 700 \mu\text{s}$)
- ◆ $I_{T(AV)} = \text{2032 A}$ ($T_C = 70^\circ\text{C}$)
- ◆ $I_{TSM} = \text{35 kA}$ ($T_j = 120^\circ\text{C}$)
- ◆ $P_{LM} = \text{25 mW}$

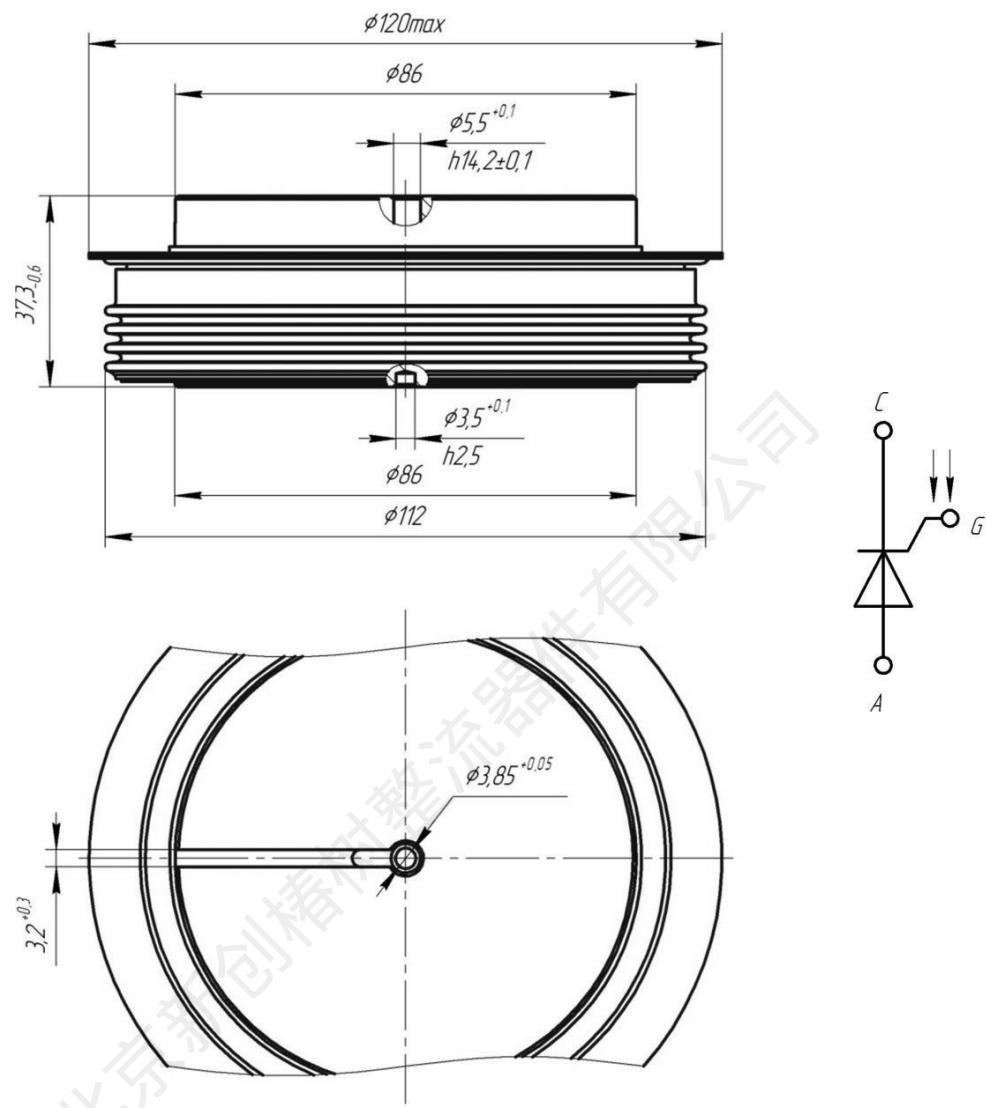
- ◆ 光触发
- ◆ 低通态和开关损耗
- ◆ 高通态电流临界上升率

**最大额定数值**

参数及测试条件	符号	数值	单位
Repetitive peak off-state voltage, $T_j = -60 \dots + 120^\circ\text{C}$	V_{DRM}	6000-6500	V
Repetitive peak reverse voltage, $T_j = -60 \dots + 120^\circ\text{C}$	V_{RRM}	6000-6500	
Direct off-state voltage, $T_j = -60 \dots + 120^\circ\text{C}$	V_D	4000-4500	
Direct reverse voltage, $T_j = -60 \dots + 120^\circ\text{C}$	V_R	4000-4500	
Repetitive peak off-state current/ Repetitive peak reverse current, $T_j = 120^\circ\text{C}$, $V_D / V_R = V_{DRM} / V_{RRM}$	I_{DRM} / I_{RRM}	250	mA
Average on-state current, $f = 50 \text{ Hz}$, double side cooling $T_C = 85^\circ\text{C}$ $T_C = 70^\circ\text{C}$	$I_{T(AV)}$	1624 2032	A
Repetitive peak on-state current, $T_j = 25^\circ\text{C}$, $V_D = V_{DRM}$ $t_p = 700 \mu\text{s}$ (single pulse) $t_p = 10 \text{ ms}$ (single pulse)	I_{TRM}	65 20	kA
Surge non-repetitive on-state current, $T_j = 120^\circ\text{C}$, $V_R = 0$, $t_p = 10 \text{ ms}$	I_{TSM}	35	kA
Critical rate of rise of on-state current, $T_j = 120^\circ\text{C}$, $V_D = 0,67V_{DRM}$, $I_T = 5000\text{A}$, $P_{LM} = 25 \text{ mW}$, $t_L = 10 \mu\text{s}$, $f = 1 \text{ Hz}$ $f = 50 \text{ Hz}$	$(di_T/dt)_{crit}$	5000 1000	A/ μs
Critical rate of rise of off-state voltage, $T_j = 120^\circ\text{C}$, $V_D = 0,67V_{DRM}$	$(dv_D/dt)_{crit}$	1000-2000	V/ μs
Minimum gate trigger light power, $T_j = 25^\circ\text{C}$, $V_D = 12 \text{ V}$	P_{LM}	25	mW
Operation junction temperature range	T_j	-40 ... +120	°C
Storage temperature range	T_{stg}	-40 ... +50	°C

电学特性					
参数及测试条件	符号	数值			单位
		min	typ.	max	
Peak on-state voltage, $T_j = 25 \text{ }^\circ\text{C}$, $I_T = 7850 \text{ A}$	V_{TM}	-	-	2,8	V
On-state threshold voltage, $T_j = 120 \text{ }^\circ\text{C}$, $I_T = 4000 - 12000 \text{ A}$	$V_{T(TO)}$	-	-	1,20	
On-state slope resistance, $T_j = 120 \text{ }^\circ\text{C}$, $I_T = 4000 - 12000 \text{ A}$	r_T	-	-	0,39	
Delay time, $T_j = 25 \text{ }^\circ\text{C}$, $V_D = 1000 \text{ V}$, $I_T = 2500 \text{ A}$, $P_{LM} = 25 \text{ mW}$, $t_L = 10 \mu\text{s}$, $t_{rise} = 0,5 \mu\text{s}$	t_d	-	-	5,0	
Turn off-time, $T_j = 120 \text{ }^\circ\text{C}$, $I_T = 2500 \text{ A}$, $di_T/dt = - 5 \text{ A}/\mu\text{s}$, $V_R \geq 100 \text{ V}$, $V_D = 0,67V_{DRM}$, $dv_D/dt = 50 \text{ V}/\mu\text{s}$	t_q	-	800	-	
Reverse recovery charge, $T_j = 120 \text{ }^\circ\text{C}$, $I_T = 2500 \text{ A}$, $di_T/dt = - 5 \text{ A}/\mu\text{s}$, $V_R \geq 100 \text{ V}$	Q_{RR}	-	-	5000	
Holding current, $T_j = 25 \text{ }^\circ\text{C}$, $V_D = 12 \text{ V}$	I_H	-	-	300	mA
Latching current, $T_j = 25 \text{ }^\circ\text{C}$, $V_D = 12 \text{ V}$, $P_{LM} = 25 \text{ mW}$, $t_L = 10 \mu\text{s}$, $t_{rise} = 0,5 \mu\text{s}$	I_L	-	-	1000	
热学特性					
Thermal junction to case resistance, sin 180°: double side cooled DC: double side cooled	$R_{th(j-c)}$ $R_{th(j-c)}$	-	-	0,0078 0,0072	$^\circ\text{C}/\text{W}$
Thermal resistance case to heatsink, double side cooled single side cooled	$R_{th(c-h)}$	-	-	0,002 0,004	
力学特性					
Weight	w	-	2,0	-	kg
Clamping force	F	60	-	80	kN
Maximum acceleration (at nominal mounting force)	a	-	-	50	m/s^2
Minimal cathode-anode distance on insulator surface	D_s	-	36	-	mm
Air strike distance	D_a	-	22	-	mm

TLI183-2000--- 外形尺寸



C – Cathode, A – Anode, G –Gate

Fig. 1. Device Outline Drawing (dimensions in mm)

Recommended optical interface cable – OA65.